



No.3442

2SK1439

N-Channel MOS Silicon FET

Very High-Speed Switching Applications

Features

- Low ON-state resistance.
 - Very high-speed switching.

Absolute Maximum Ratings at $T_a = 25^\circ\text{C}$

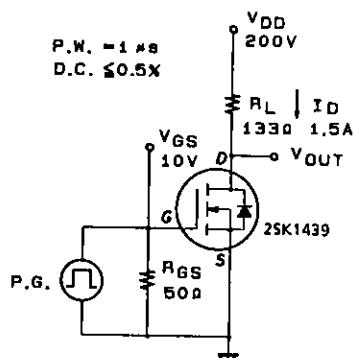
Absolute Maximum Ratings at $T_d = 25^\circ\text{C}$		unit
Drain to Source Voltage	V_{DSS}	450 V
Gate to Source Voltage	V_{GSS}	± 30 V
Drain Current(DC)	I_D	3 A
Drain Current(Pulse)	I_{DP}	PW $\leq 10\ \mu\text{s}$, duty cycle $\leq 1\%$ 12 A
Allowable Power Dissipation	P_D	Tc = 25°C 50 W
		1.75 W
Channel Temperature	T_{ch}	150 $^\circ\text{C}$
Storage Temperature	T_{stg}	-55 to +150 $^\circ\text{C}$

Electrical Characteristics at Ta = 25°C

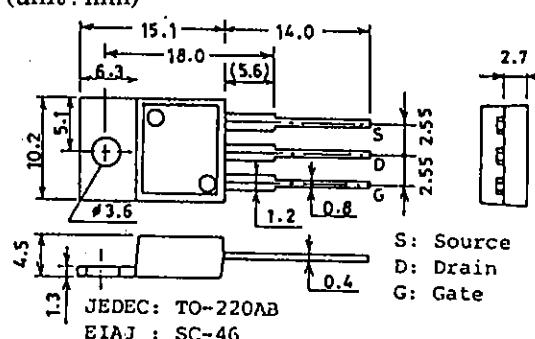
Electrical Characteristics at $T_A = 25^\circ C$			min	typ	max	unit
D-S Breakdown Voltage	$V_{(BR)DSS}$	$I_D = 1\text{mA}, V_{GS} = 0$	450			V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = 450\text{V}, V_{GS} = 0$		1.0		mA
Gate to Source Leakage Current	I_{GSS}	$V_{GS} = \pm 30\text{V}, V_{DS} = 0$			± 100	nA
Cutoff Voltage	$V_{GS(\text{off})}$	$V_{DS} = 10\text{V}, I_D = 1\text{mA}$	2.0		3.0	V
Forward Transfer Admittance	$ Y_{fs} $	$V_{DS} = 10\text{V}, I_D = 1.5\text{A}$	1.0	2.0		S
Static Drain to Source on State Resistance	$R_{DS(on)}$	$I_D = 1.5\text{A}, V_{GS} = 10\text{V}$		2.0	2.6	Ω
Input Capacitance	C_{iss}	$V_{DS} = 20\text{V}, f = 1\text{MHz}$	400			pF
Output Capacitance	C_{oss}	$V_{DS} = 20\text{V}, f = 1\text{MHz}$	60			pF
Reverse Transfer Capacitance	C_{rss}	$V_{DS} = 20\text{V}, f = 1\text{MHz}$	25			pF
Turn-ON Delay Time	$t_{d(on)}$			12		ns
Rise Time	t_r	$I_D = 1.5\text{A}, V_{GS} = 10\text{V}$		20		ns
Turn-OFF Delay Time	$t_{d(off)}$	$V_{DD} = 200\text{V}, R_{GS} = 50\Omega$		80		ns
Fall Time	t_f			35		ns
Diode Forward Voltage	V_{SD}	$I_S = 3\text{A}, V_{GS} = 0$		1.8		V

(Note) Be careful in handling the 2SK1439 because it has no protection diode between gate and source.

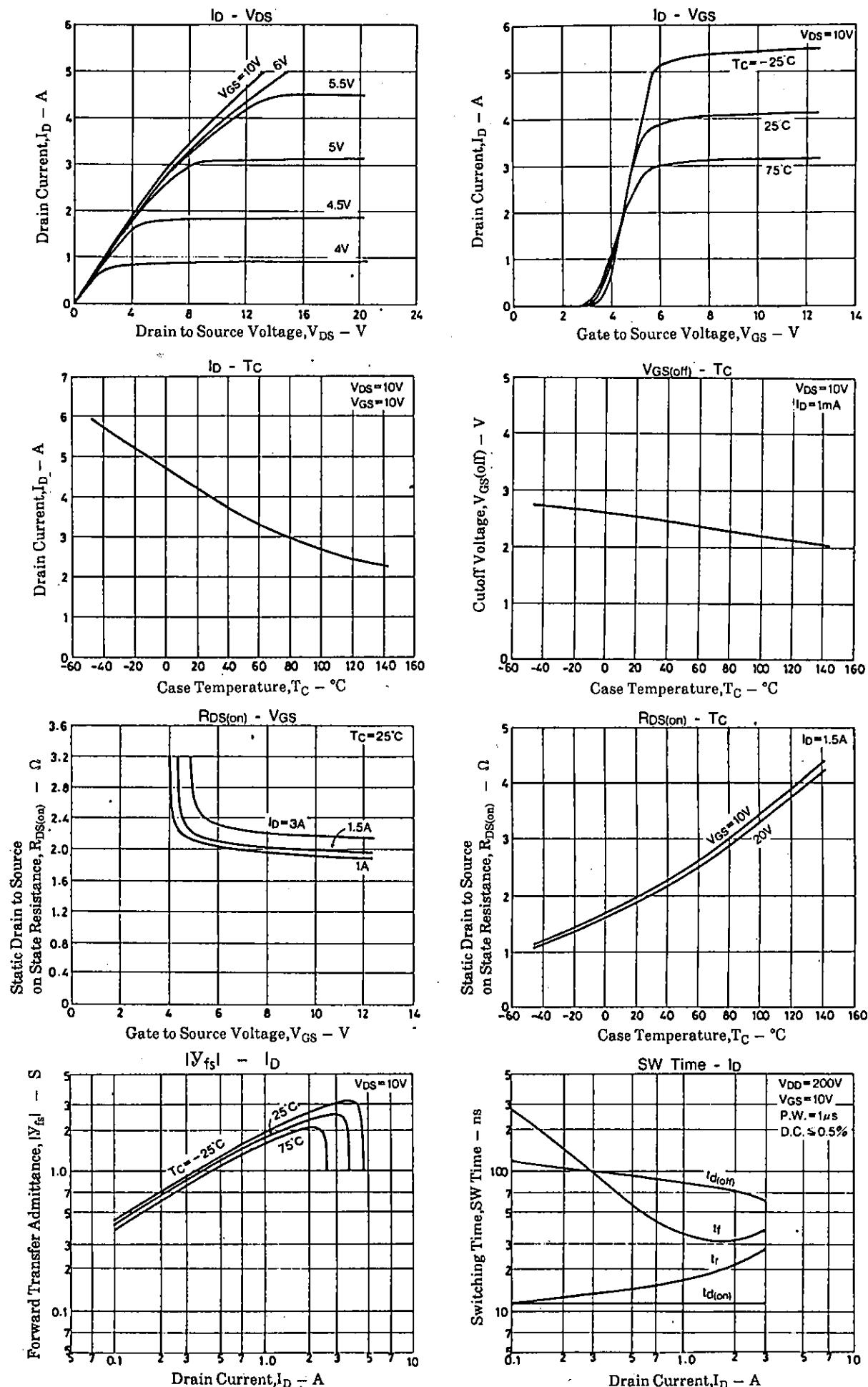
Switching Time Test Circuit

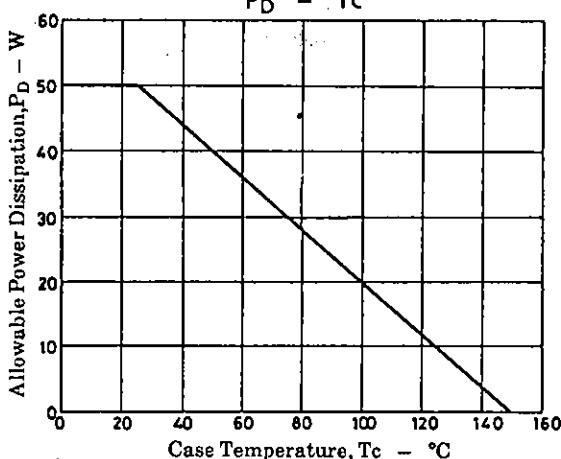
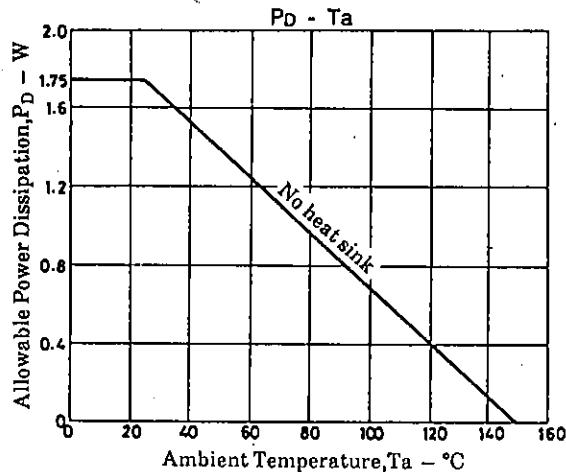
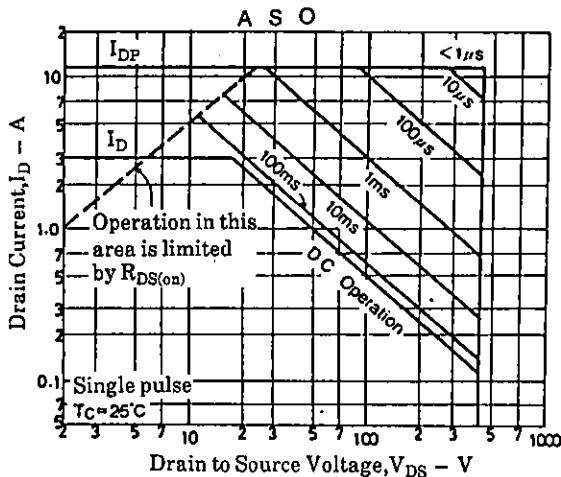
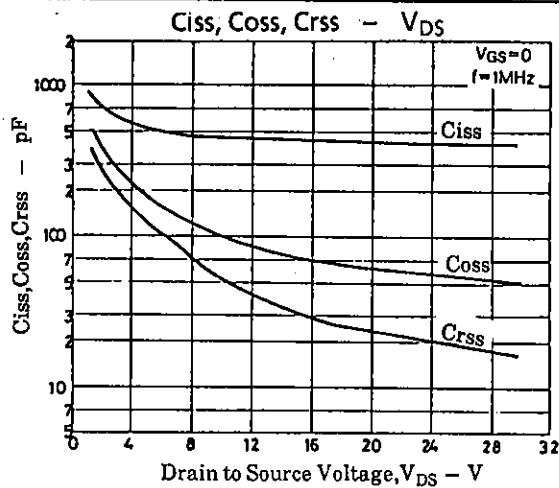


Package Dimensions 2052B (unit : mm)



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